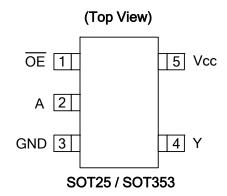


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Description

The 74AHCT1G125 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a HIGH-level is applied to the output enable (\overline{OE}) pin. The device is designed for operation with a power supply range of 4.5V to 5.5V.

Pin Assignments



Features

- Supply Voltage Range from 4.5V to 5.5V
- ± 8 mA Output Drive at 5.0V
- CMOS low power consumption
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time.
- ESD Protection per JESD 22
 - o Exceeds 200-V Machine Model (A115-A)
 - Exceeds 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at

Latch-Up Exceeds 100mA per JESD 78, Class II

http://www.diodes.com/products/lead_free.html.

- SOT25 and SOT353: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish / RoHS Compliant (Note 1)

Applications

- General Purpose Logic
- Wide array of products such as:
 - o PCs, networking, notebooks, netbooks, PDAs
 - o Computer peripherals, hard drives, CD/DVD ROM
 - o TV, DVD, DVR, set top box
 - o Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders

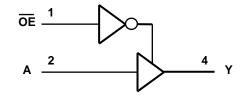


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Pin Descriptions

Pin Name	Pin No.	Description
ŌE	1	Output Enable
А	2	Data Input
GND	3	Ground
Y	4	Data Output
V _{CC}	5	Supply Voltage

Logic Diagram



Function Table

Inp	Output	
OE	Α	Y
L	Н	Н
L	L	L
Н	Х	Z



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	-20	mA
I _{OK}	Output Clamp Current ($V_O < 0$ or $V_O > V_{CC}$)	±20	mA
lo	Continuous output current ($V_O = 0$ to V_{CC})	±25	mA
I _{CC}	Continuous current through V _{CC}	50	mA
I _{GND}	Continuous current through GND	-50	mA
TJ	TJ Operating Junction Temperature		°C
T _{STG} Storage Temperature		-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 3)

Symbol		Parameter	Min	Max	Unit
V _{CC}	Operating Voltage		4.5	5.5	V
V _{IH}	High-level Input Voltage		2.0		V
VIL	Low-level input voltage			0.8	V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
I _{ОН}	High-level output current			-8	mA
I _{OL}	Low-level output current			8	mA
Δt/ΔV	Input transition rise or fall rate			20	ns/V
T _A	Operating free-air temperature		-40	125	٥C

Notes: 3. Unused inputs should be held at V_{CC} or Ground.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Electrical Characteristics

O	Demonstern	Test Osmilitiens	N		25⁰C		-40ºC t	o 85⁰C	-40°C to	o 125⁰C	11
Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Min	Max	Min	Max	Unit
.,	High Level	I _{OH} = -50μA	4.5V	4.4	4.5		4.4		4.4		
V _{OH}	Output Voltage	I _{OH} = -8mA	4.5V	3.94			3.8		3.70		V
V	Low Level	I _{OL} = 50μA	4.5V		0	0.1		0.1		0.1	V
V _{OL}	Output Voltage	$I_{OL} = 8mA$	4.5V			0.36		0.44		0.55	v
lı –	Input Current	$V_I = 5.5V$ or GND	0 to 5.5V			±0.1		±1		±2	μA
I _{OZ}	Z State Leakage Current	V _O =0 to 5.5V	5.5V			0.25		2.5		10	μΑ
I _{CC}	Supply Current	V _I = 5.5V or GND I _O =0	5.5V			1		10		40	μA
Ci	Input Capacitance	V _I = V _{CC} – or GND	5.5V		2.0	10		10		10	pF
ΔI _{CC}	Additional Supply Current	One input at 3.4 V Other inputs at V _{CC} or GND	5.5V			1.35		1.5			mA
0	Thermal Resistance	SOT25			204						0000
θ_{JA}	Junction-to- Ambient	SOT353	(Note 4)		371						°C/W
0	Thermal Resistance	SOT25			52						°0.44
θ _{JC}	Junction-to- Case	SOT353	(Note 4)		143						°C/W

Note: 4. Test conditions for SOT25, and SOT353: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Switching Characteristics

$V_{CC} = 5V \pm 0.5V$ (see Figure 1)

Parameter	From	то			25⁰C		-40ºC t	o 85ºC	-40°C to	o 125⁰C	Unit
Farameter	(Input)	(OUTPUT)		Min	Тур.	Max	Min	Max	Min	Max	Unit
+ .	Δ	V	C _L =15pF	0.6	3.4	5.5	0.6	6.5	0.6	7.0	ns
t _{pd}	A	Y	$C_L=50pF$	0.6	4.7	7.5	0.6	8.5	0.6	9.5	ns
		V	C _L =15pF	0.6	3.6	5.6	0.6	6.3	0.6	7.0	ns
t _{en}	OE	Ŷ	C _L =50pF	0.6	5.4	8.0	0.6	9.0	0.6	9.5	ns
4		V	C _L =15pF	0.6	4.3	6.8	0.6	8.0	0.6	8.5	ns
t _{dis}	OE	Y	C _L =50pF	0.6	6.1	8.8	0.6	10.0	0.6	11.0	ns

Operating Characteristics

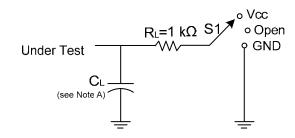
$T_A = 25 \ ^{o}C$

Parameter		Parameter	Test Conditions	V _{CC} = 5 V Typ.	Unit
0	C _{pd}	Power dissipation capacitance	f = 1 MHz No Load	14	pF



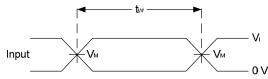
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information

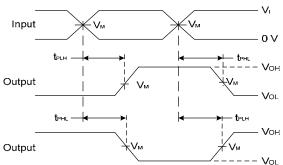


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

Maa	In	puts	V	C	MA	
Vcc	VI	t _r /t _f	V _M	υL	VΔ	
5V±0.5V	V _{CC}	≤3ns	V _{CC} /2	15pF	0.3V	
5V±0.5V	V _{CC}	≤3ns	V _{CC} /2	50pF	0.3V	



Voltage Waveform Pulse Duration





Output V™ Vм Control 0 V Output tezi – te VLOAD/2 Waveform 1 S1 at VLOAD Vol + Va (see Note B) Voi → t_{РZH} → 🗲 tenz Output Vон Waveform 2 Он И ∠∨м S1 at GND (see Note B) 6 OV

Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1. Load Circuit and Voltage Waveforms

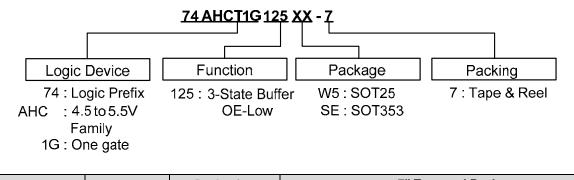
- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate \leq 1 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
 - E. t_{PZL} and t_{PZH} are the same as t_{EN} .
 - F. t_{PLH} and t_{PHL} are the same as t_{PD}

Vi



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

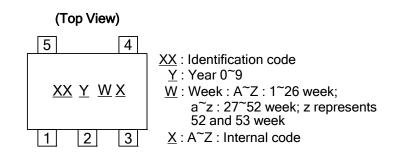
Ordering Information



	Device	Package	Packaging	7" Tape	and Reel
	Device	Code	(Note 5)	Quantity	Part Number Suffix
Pb ,	74AHCT1G125W5-7	W5	SOT25	3000/Tape & Reel	-7
B ,	74AHCT1G125SE-7	SE	SOT353	3000/Tape & Reel	-7

Notes: 5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Marking Information



Part Number	Package	Identification Code	
74AHCT1G125W5	SOT25	ZY	
74AHCT1G125SE	SOT353	ZY	

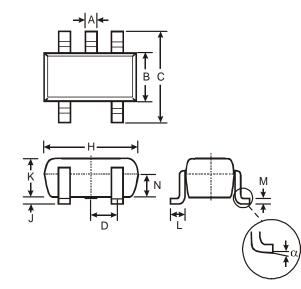
74AHCT1G125 Document number: DS35186Rev. 1 - 2



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

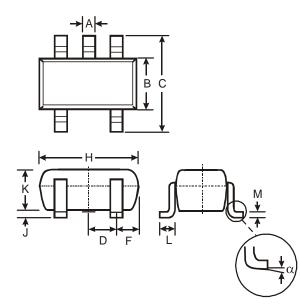
Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



	SOT25							
Dim	Min	Max	Тур					
Α	0.35	0.50	0.38					
В	1.50	1.70	1.60					
С	2.70	3.00	2.80					
D	_	_	0.95					
Н	2.90	3.10	3.00					
J	0.013	0.10	0.05					
Κ	1.00	1.30	1.10					
L	0.35	0.55	0.40					
М	0.10	0.20	0.15					
Ν	0.70	0.80	0.75					
α	0°	8°	_					
Ali D	imensi	ons in	mm					

(2) Package Type: SOT353



SOT353		
Dim	Min	Max
Α	0.10	0.30
В	1.15	1.35
c	2.00	2.20
D	0.65 Тур	
F	0.40	0.45
Н	1.80	2.20
ر	0	0.10
К	0.90	1.00
L	0.25	0.40
М	0.10	0.22
α	0°	8°
All Dimensions in mm		

74AHCT1G125 Document number: DS35186Rev. 1 - 2



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SINGLE BUFFER GATE WITH 3-STATE OUTPUT

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